

**Amendments to the Claims:**

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1-80. (Canceled)

81. (New) A thin film patterning substrate, comprising:

a substrate;

banks, each of which includes an organic substance at least on its surface, said banks being formed above said substrate and partitioning a surface of the substrate into a plurality of areas, each of said areas including an inorganic substance; and

a thin film arranged in at least one of said areas, the thin film being made from a fluid,

wherein said banks exhibit non-affinity for the fluid, said non-affinity being greater than that of said partitioned areas.

82. (New) The thin film patterning substrate according to claim 81, wherein said inorganic substance is selected from a group consisting of an ITO, a glass and a crystal.

83. (New) The thin film patterning substrate according to claim 81, wherein said organic substance includes polyimide.

84. (New) The thin film patterning substrate according to claim 81, wherein said banks have heights of between about 1  $\mu\text{m}$  and about 2  $\mu\text{m}$ , while said thin film has a thickness between about 0.05  $\mu\text{m}$  and about 0.2  $\mu\text{m}$ .

85. (New) The thin film patterning substrate according to claim 81, wherein the banks include a side surface and an upper surface both of which include said organic substance.

86. (New) The thin film patterning substrate according to claim 81, wherein a contact angle of said fluid to the surface of said banks is about 50° or greater, while to the surface of said partitioned areas is about 30° or less.

87. (New) The thin film patterning substrate according to claim 81, wherein said thin film includes a colored resin.

88. (New) The thin film patterning substrate according to claim 81, wherein said thin film includes an organic semiconductor material.

89. (New) The thin film patterning substrate according to claim 81, wherein said thin film is formed as a multi-layer structure.

90. (New) The thin film patterning substrate according to claim 89, wherein said thin film includes at least one of a light emitting layer, a hole injection layer and an electron injection layer.

91. (New) The thin film patterning substrate according to claim 81, further comprising a thin film transistor formed above said substrate.

92. (New) A thin film patterning substrate, comprising:  
a substrate;  
banks being formed above said substrate and partitioning a surface of the substrate into a plurality of areas, said banks comprising a first layer including an inorganic substance and a second layer including an organic substance;  
a thin film arranged in at least one of said areas, the thin film being made from a fluid, wherein said banks exhibit non-affinity for the fluid, said non-affinity being greater than that of said partitioned areas.

93. (New) The thin film patterning substrate according to claim 92, wherein said first layer is disposed above said substrate and wherein said second layer is disposed above said first layer.

94. (New) The thin film patterning substrate according to claim 92, wherein said first layer exhibits affinity for the fluid which is greater than that of said second layer.

95. (New) The thin film patterning substrate according to claim 92, wherein a surface of said partitioned areas exhibits affinity for the fluid which is equal to or greater than that of said first layer.

96. (New) The thin film patterning substrate according to claim 95, wherein the surface of said partitioned areas includes an inorganic substance.

97. (New) The thin film patterning substrate according to claim 92, wherein a contact angle of said fluid to the surface of said first layer is between about 20° and about 50°, to the second layer is about 50° or greater, and to the surface of said partitioned areas is about 30° or less.

98. (New) The thin film patterning substrate according to claim 92, wherein said first layer includes a material selected from a group consisting of a silicon oxide, a silicon nitride and an amorphous silicon.

99. (New) The thin film patterning substrate according to claim 92, wherein said inorganic substance is selected from a group consisting of an ITO, a glass and a crystal.

100. (New) The thin film patterning substrate according to claim 92, wherein said organic substance includes polyimide.

101. (New) The thin film patterning substrate according to claim 92, wherein said banks have heights of between about 1  $\mu\text{m}$  and about 2  $\mu\text{m}$ , while said thin film has a thickness between about 0.05  $\mu\text{m}$  and about 0.2  $\mu\text{m}$ .

102. (New) The thin film patterning substrate according to claim 92, wherein a thickness of said thin film is approximately equal to that of the first layer.

103. (New) The thin film patterning substrate according to claim 92, wherein said thin film includes an organic semiconductor material.

104. (New) The thin film patterning substrate according to claim 92, wherein said thin film includes a colored resin.

105. (New) The thin film patterning substrate according to claim 92, further comprising a thin film transistor formed above said substrate.

106. (New) A thin film patterning substrate, comprising:

a substrate;

banks being formed above said substrate and partitioning a surface of the substrate into a plurality of areas, said banks comprising a first layer and a second layer;

a thin film arranged in at least one of said areas, the thin film being made from a fluid, wherein a surface of said first layer exhibits affinity for the fluid which is greater than that of said second layer.

107. (New) The thin film patterning substrate according to claim 106, wherein a surface of said partitioned areas exhibits affinity for the fluid that is equal to or greater than that of said first layer.

108. (New) An EL device comprising:

a substrate;

banks, each of which includes an organic substance at least on a surface, said banks being formed above said substrate and partitioning a surface of the substrate into a plurality of areas, each of said areas including an inorganic substance; and

a semiconductor material being capable of emitting light and arranged in at least one of said areas, the semiconductor material being made from a fluid, wherein said banks exhibit non-affinity for the fluid, said non-affinity being greater than that of said partitioned areas.

109. (New) The EL device according to claim 108, further comprising a plurality of semiconductor materials, each of which is capable of emitting light different in color and disposed in a respective one of the areas.

110. (New) An EL device comprising:

a substrate;

banks being formed above said substrate and partitioning a surface of the substrate into a plurality of areas, said banks comprising a first layer including an inorganic substance and a second layer including an organic substance;

a semiconductor material being capable of emitting light and arranged in at least one of said areas, the semiconductor material being made from a fluid, wherein said banks exhibit non-affinity for the fluid, said non-affinity being greater than that of said partitioned areas.

111. (New) The EL device according to claim 110, further comprising a plurality of semiconductor materials, each of which is capable of emitting light different in color and disposed in a respective one of the areas.

112. (New) A thin film patterning substrate, comprising:

a substrate;

banks being formed above said substrate and partitioning a surface of the substrate into a plurality of areas, said banks comprising a first layer and a second layer;

a semiconductor material being capable of emitting light and arranged in at least one of said areas, the semiconductor material being made from a fluid,

wherein a surface of said first layer exhibits affinity for the fluid which is greater than that of said second layer.

113. (New) The thin film patterning substrate according to claim 112, wherein a surface of said partitioned areas exhibits affinity for the fluid that is equal to or greater than that of said first layer.

114. (New) The EL device according to claim 113, further comprising a plurality of semiconductor materials, each of which is capable of emitting light different in color and disposed in a respective one of the areas.

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